

Qinglong Yan

List of Publications by Year in descending order

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6
papers

374
citations

1478505

6
h-index

1872680

6
g-index

6
all docs

6
docs citations

6
times ranked

264
citing authors

#	ARTICLE	IF	CITATIONS
1	Lateral AlGaIn MOSFETs With High Power Figure of Merit of 277 MW/cm^2 . IEEE Electron Device Letters, 2020, 41, 537-540.	3.9	89
2	High-Performance Vertical AlGaIn Schottky Barrier Diode With Implanted Edge Termination. IEEE Electron Device Letters, 2019, 40, 1788-1791.	3.9	84
3	AlGaIn hetero-junction barrier Schottky diode with reverse leakage current modulation and $\text{BV}^2/\text{Ron,sp}$ value of 0.93 GW/cm^2 . Applied Physics Letters, 2021, 118, .	3.3	72
4	6 kV/3.4 m^2/cm^2 Vertical AlGaIn Schottky Barrier Diode With $\text{BV}^2/\text{Ron,sp}$ Performance Exceeding 1-D Unipolar Limit of GaN and SiC. IEEE Electron Device Letters, 2022, 43, 765-768.	3.9	65
5	Low density of interface trap states and temperature dependence study of AlGaIn Schottky barrier diode with p-NiOx termination. Applied Physics Letters, 2022, 120, .	3.3	38
6	Impact of Implanted Edge Termination on Vertical AlGaIn Schottky Barrier Diodes Under OFF-State Stressing. IEEE Transactions on Electron Devices, 2020, 67, 3948-3953.	3.0	26